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27. (amended) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

32. (amended) The composition of claim 26, wherein said composition does not remove side wall spacers of a gate stack which is also formed over said substrate.

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33. (amended) The composition of claim 26, wherein the flow rate ratio of said fluorocarbon to said ammonia is not less than about 3:1.

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35. (amended) The composition of claim 34, wherein said flow rate ratio is within the range of about 4:1 to about 10:1.

Please add new claims 71 and 72.

71. (new) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

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a gaseous mixture consisting of at least one fluorocarbon and ammonia flowed into a reaction chamber, said reaction chamber having an operating pressure of from about 30 to about 60 milliTorr, wherein the flow rate ratio of said at least one fluorocarbon to said ammonia is from about 2:1 to about 40:1.

72. (new) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

By end
a gaseous mixture consisting of at least one fluorocarbon and ammonia.